MBT2222ADW1, NSVBT2222ADW1

General Purpose Transistor

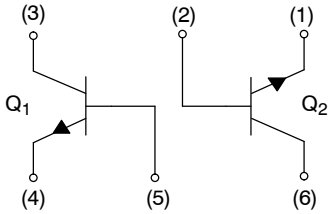
NPN Silicon

ON Semiconductor®

http://onsemi.com

Features

- Moisture Sensitivity Level: 1
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant



SC−88/SC70−6/SOT−363
CASE 419B
STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	40	Vdc
Collector−Base Voltage	V_{CBO}	75	Vdc
Emitter−Base Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous	I_C	600	mAdc
Electrostatic Discharge	ESD	HBM Class 2 MM Class B	

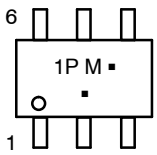
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Package Dissipation (Note 1), T_A = 25°C	P_D	150	mW
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	833	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.

MARKING DIAGRAM



1P = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MBT2222ADW1T1G	SOT−363 (Pb−Free)	3000 / Tape & Reel
NSVBT2222ADW1T1G	SOT−363 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage	(I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	−	Vdc
Collector−Base Breakdown Voltage	(I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	75	−	Vdc
Emitter−Base Breakdown Voltage,	(I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	−	Vdc
Collector Cutoff Current	(V_{CE} = 60 Vdc, $V_{EB(off)}$ = 3.0 Vdc)	I_{CEX}	−	10	nAdc
Collector Cutoff Current	(V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0, T_A = 125°C)	I_{CBO}	 − −	 0.01 10	μAdc
Emitter Cutoff Current	(V_{EB} = 3.0 Vdc, I_C = 0)	I_{EBO}	−	100	nAdc
Base Cutoff Current	(V_{CE} = 60 Vdc, $V_{EB(off)}$ = 3.0 Vdc)	I_{BL}	−	20	nAdc
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			−
	(I_C = 0.1 mAdc, V_{CE} = 10 Vdc)		35	−	
	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)		50	−	
	(I_C = 10 mAdc, V_{CE} = 10 Vdc)		75	−	
	(I_C = 10 mAdc, V_{CE} = 10 Vdc, T_A = −55°C)		35	−	
	(I_C = 150 mAdc, V_{CE} = 10 Vdc) (Note 2)		100	300	
	(I_C = 150 mAdc, V_{CE} = 1.0 Vdc) (Note 2)		50	−	
	(I_C = 500 mAdc, V_{CE} = 10 Vdc) (Note 2)		40	−	
Collector−Emitter Saturation Voltage (Note 2)		$V_{CE(sat)}$			Vdc
	(I_C = 150 mAdc, I_B = 15 mAdc)		−	0.3	
	(I_C = 500 mAdc, I_B = 50 mAdc)		−	1.0	
Base−Emitter Saturation Voltage (Note 2)		$V_{BE(sat)}$			Vdc
	(I_C = 150 mAdc, I_B = 15 mAdc)		0.6	1.2	
	(I_C = 500 mAdc, I_B = 50 mAdc)		−	2.0	
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product (Note 3)	(I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	300	−	MHz
Output Capacitance	(V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	−	8.0	pF
Input Capacitance	(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	−	25	pF
Input Impedance		h_{ie}			kΩ
	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		2.0	8.0	
	(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		0.25	1.25	
Voltage Feedback Ratio		h_{re}			X 10^{-4}
	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		−	8.0	
	(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		−	4.0	
Small−Signal Current Gain		h_{fe}			−
	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		50	300	
	(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		75	375	
Output Admittance		h_{oe}			μmhos
	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		5.0	35	
	(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		25	200	
Collector Base Time Constant	(I_E = 20 mAdc, V_{CB} = 20 Vdc, f = 31.8 MHz)	rb, C_c	−	150	ps
Noise Figure	(I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	NF	−	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = −0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	−	10	ns
Rise Time		t_r	−	25	
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	−	225	ns
Fall Time		t_f	−	60	

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
3. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

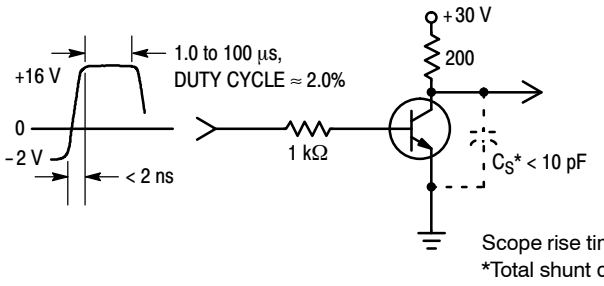
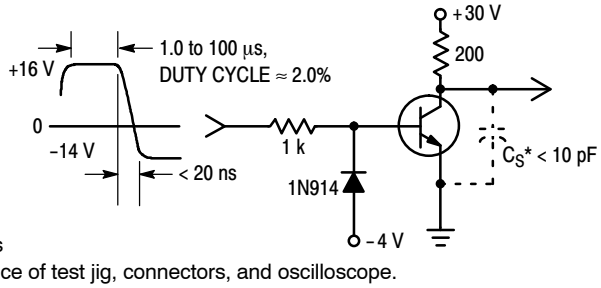


Figure 1. Turn−On Time



Scope rise time < 4 ns
*Total shunt capacitance of test jig, connectors, and oscilloscope.

Figure 2. Turn−Off Time

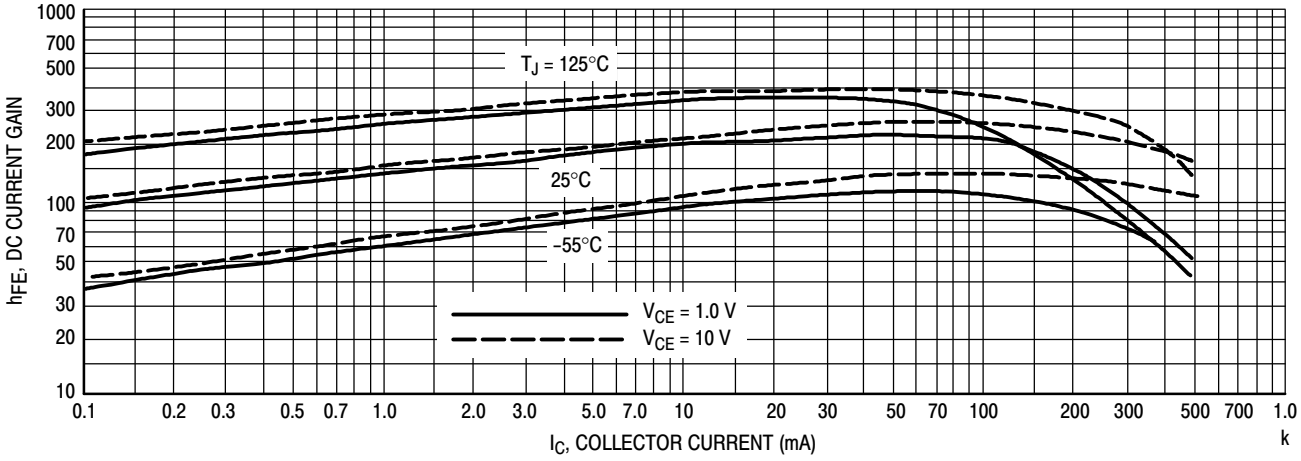


Figure 3. DC Current Gain

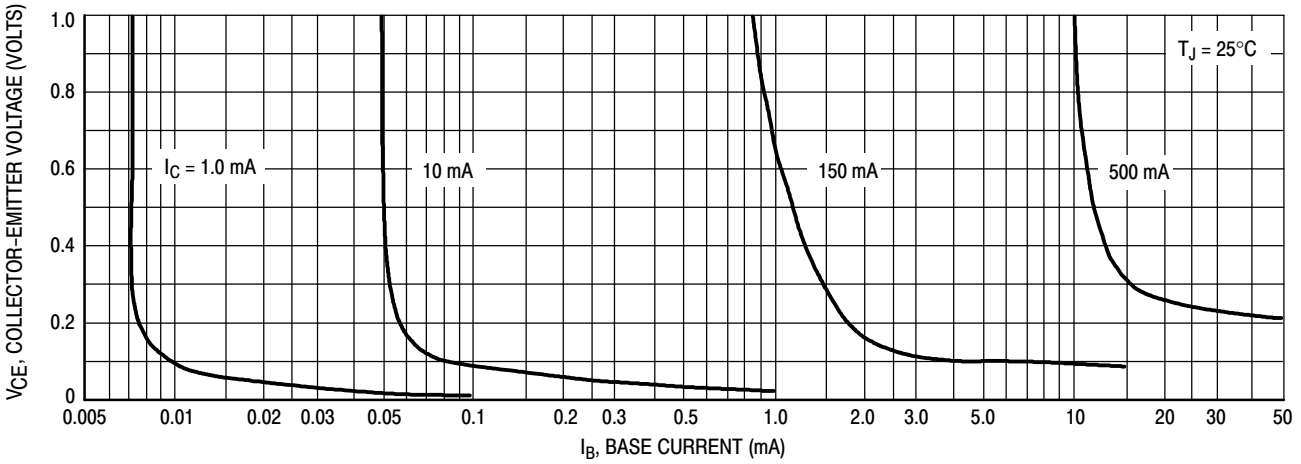


Figure 4. Collector Saturation Region

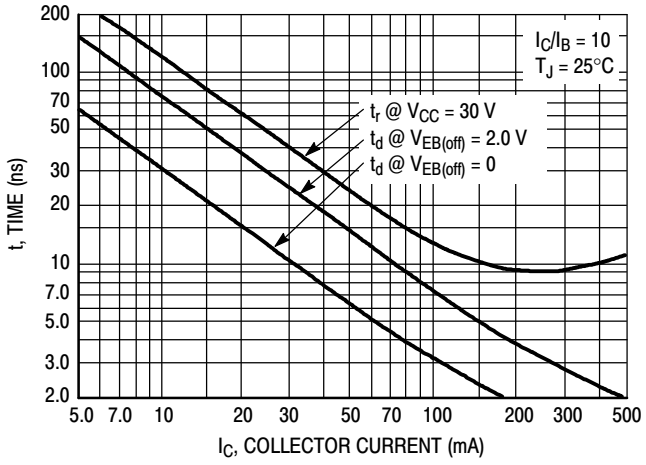


Figure 5. Turn−On Time

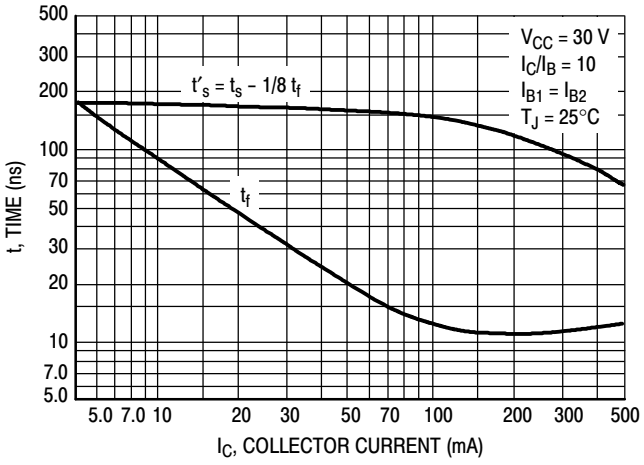


Figure 6. Turn−Off Time

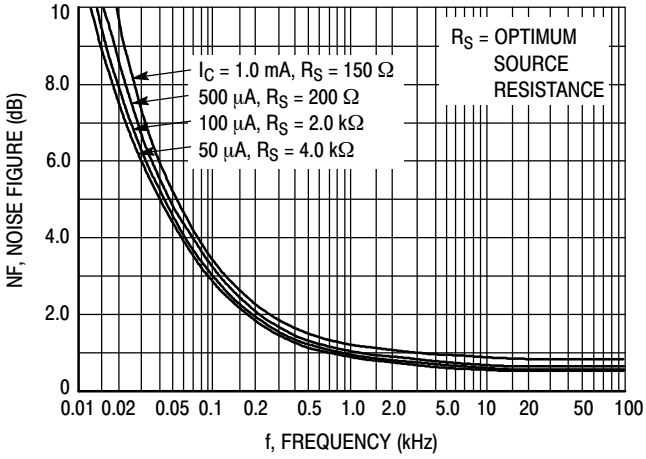


Figure 7. Frequency Effects

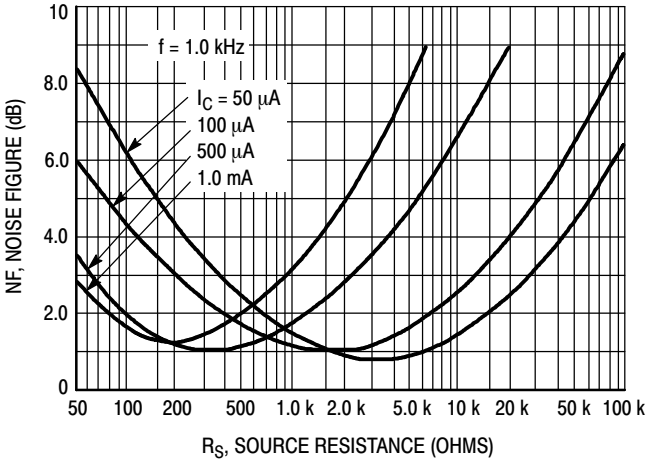


Figure 8. Source Resistance Effects

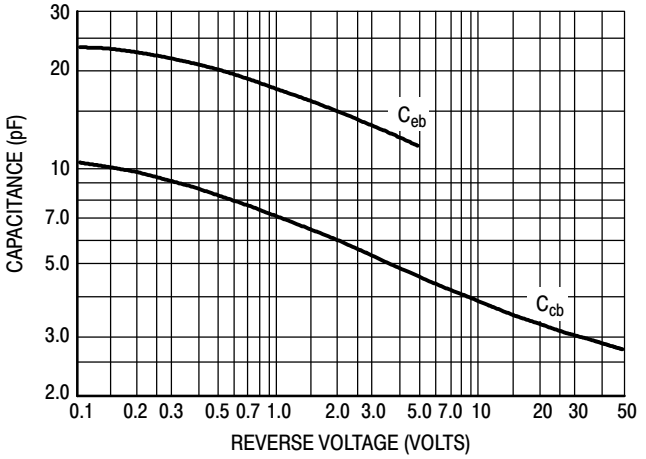


Figure 9. Capacitances

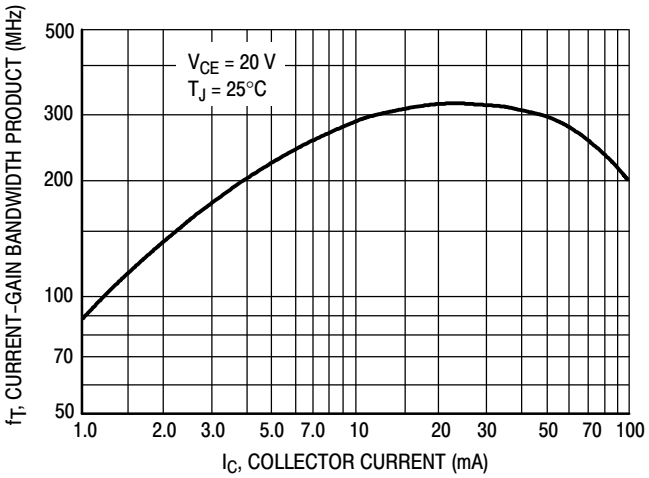


Figure 10. Current−Gain Bandwidth Product

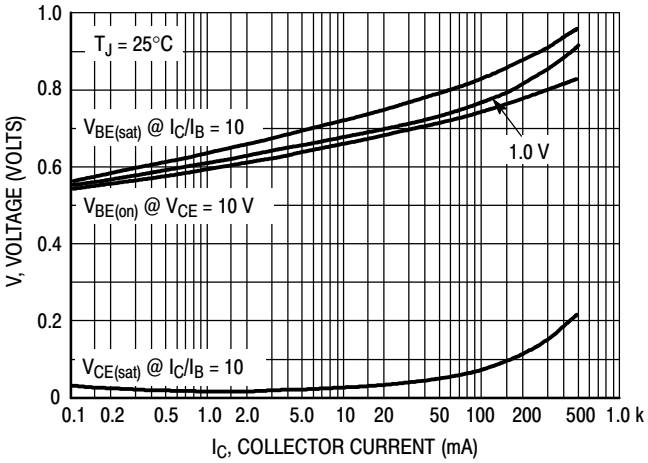


Figure 11. “On” Voltages

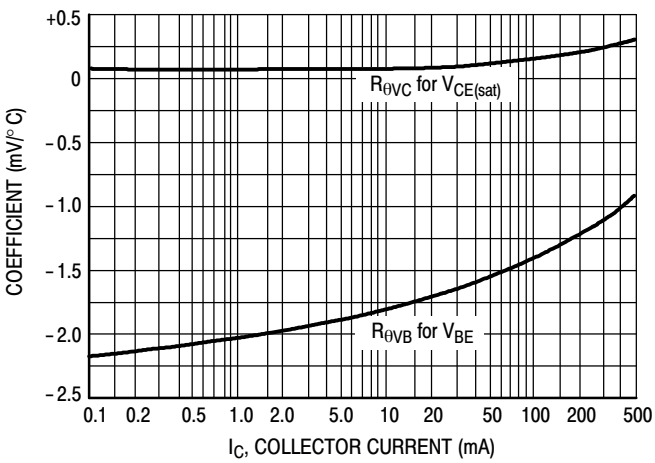
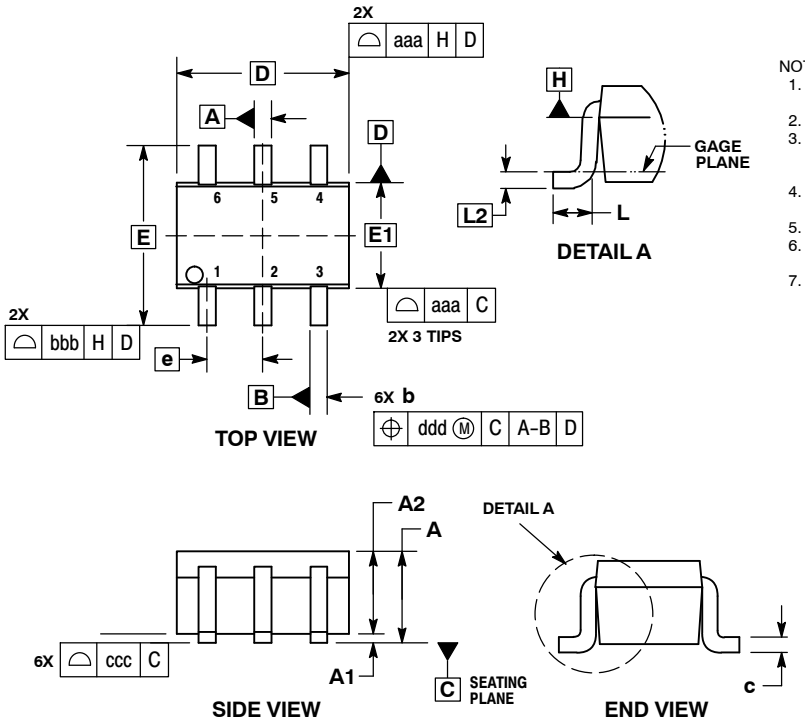


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y

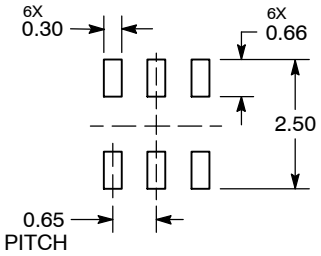


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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